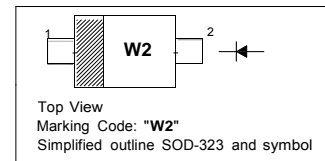


## Silicon Epitaxial Planar Switching Diode

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	40	V
Reverse Voltage	$V_R$	40	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	$I_{FM}$	600	mA
Non-Repetitive Peak Forward Surge Current ( $t = 1\text{ s}$ )	$I_{FSM}$	1	A
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	1.1	V
Reverse Current at $V_R = 15\text{ V}$ at $V_R = 35\text{ V}$	$I_R$	50 500	nA
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	4	pF
Reverse Recovery Time at $V_R = 6\text{ V}$ , $I_F = 10\text{ mA}$ , $I_{rr} = 0.1 \cdot I_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	10	ns



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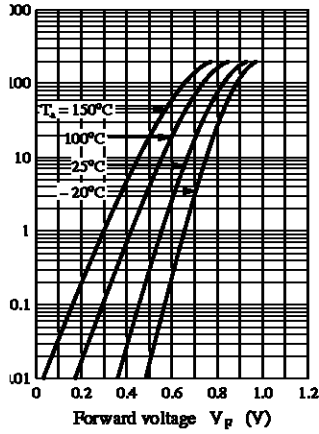
# SOD-323

# 1ST112WS

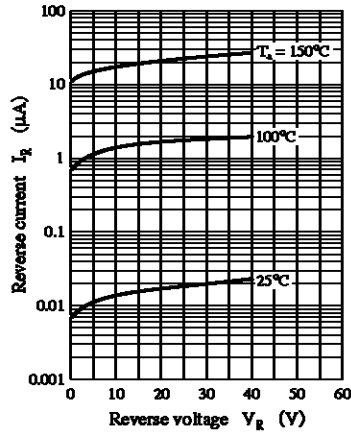


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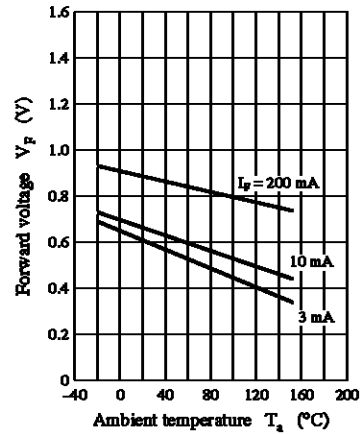
$I_F - V_F$



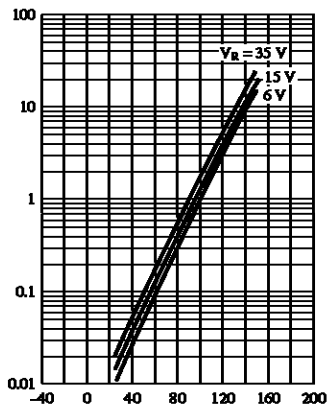
$I_R - V_R$



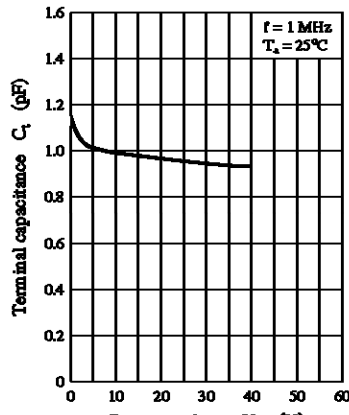
$V_F - T_a$



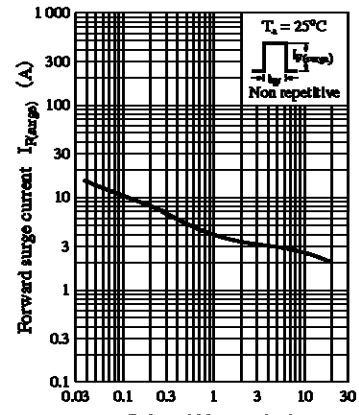
$I_R - T_a$



$C_t - V_R$



$I_{F(\text{surge})} - t_w$

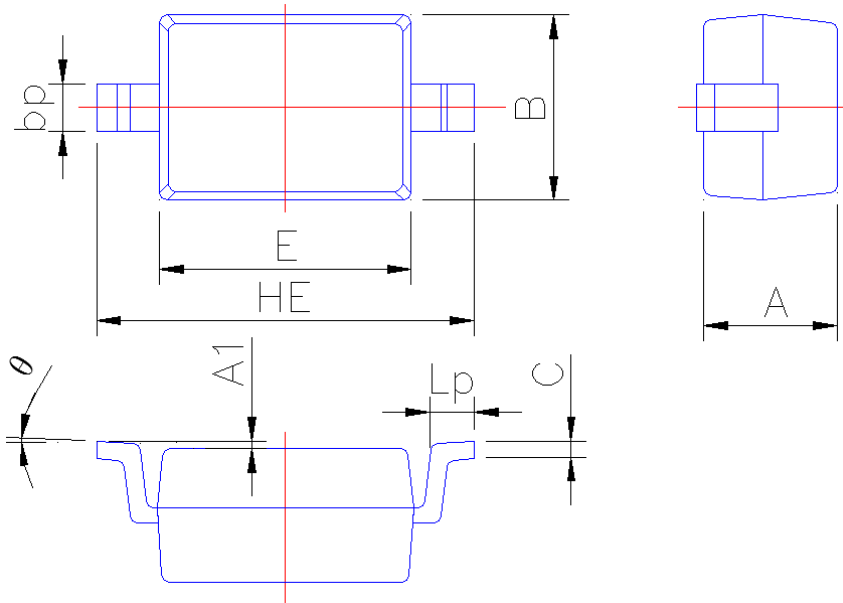




## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°